

IRFR3711ZPbF
IRFU3711ZPbF

HEXFET® Power MOSFET

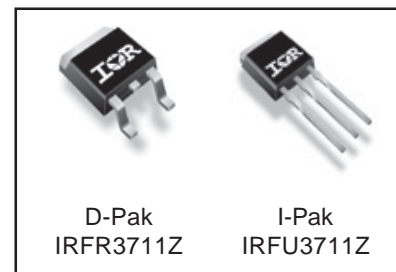
Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- Lead-Free

V_{DSS}	R_{DS(on)} max	Qg
20V	5.7mΩ	18nC

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	20	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	93 [ⓐ]	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	66 [ⓐ]	
I _{DM}	Pulsed Drain Current [ⓑ]	370	
P _D @ T _C = 25°C	Maximum Power Dissipation [ⓒ]	79	W
P _D @ T _C = 100°C	Maximum Power Dissipation [ⓒ]	39	
	Linear Derating Factor	0.53	W/°C
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.9	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount) [ⓑ]	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

Notes [ⓐ] through [ⓒ] are on page 11

IRFR/U3711ZPbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	13	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.5	5.7	mΩ	$V_{GS} = 10V, I_D = 15A$ ③
		—	6.2	7.8		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.55	2.0	2.45	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-5.4	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	48	—	—	S	$V_{DS} = 10V, I_D = 12A$
Q_g	Total Gate Charge	—	18	27	nC	$V_{DS} = 10V$ $V_{GS} = 4.5V$ $I_D = 12A$ See Fig. 16
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	5.1	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.8	—		
Q_{gd}	Gate-to-Drain Charge	—	6.5	—		
Q_{godr}	Gate Charge Overdrive	—	4.6	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	8.3	—		
Q_{oss}	Output Charge	—	9.8	—	nC	$V_{DS} = 10V, V_{GS} = 0V$
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ② $I_D = 12A$ Clamped Inductive Load
t_r	Rise Time	—	13	—		
$t_{d(off)}$	Turn-Off Delay Time	—	15	—		
t_f	Fall Time	—	5.2	—		
C_{iss}	Input Capacitance	—	2160	—	pF	$V_{GS} = 0V$ $V_{DS} = 10V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	700	—		
C_{riss}	Reverse Transfer Capacitance	—	360	—		

Avalanche Characteristics

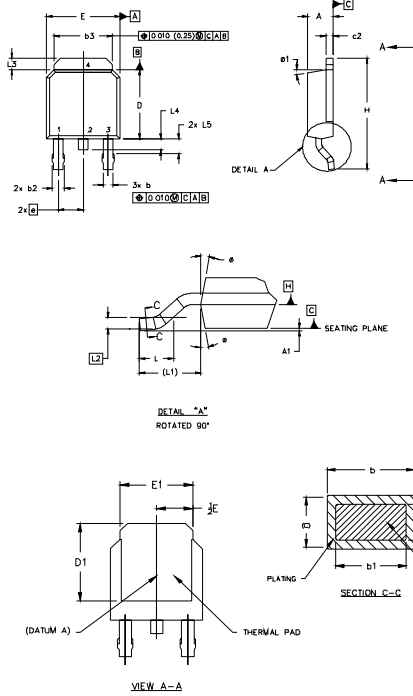
	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	140	mJ
I_{AR}	Avalanche Current ①	—	12	A
E_{AR}	Repetitive Avalanche Energy ①	—	7.9	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	93 ④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	370		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 12A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	19	28	ns	$T_J = 25^\circ\text{C}, I_F = 12A, V_{DD} = 10V$
Q_{rr}	Reverse Recovery Charge	—	9.4	14	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.75	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.051 BSC		0.020 BSC		
L3	0.89	1.27	.035	.050	
L4	1.14	1.02	.045	.040	
L5	1.14	1.52	.045	.060	3
a	0"	10"	0"	10"	
a1	0"	15"	0"	15"	

LEAD ASSIGNMENTS

HEFFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

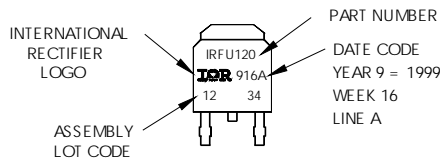
IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

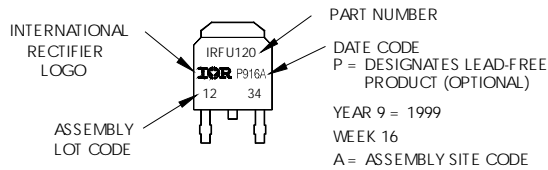
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

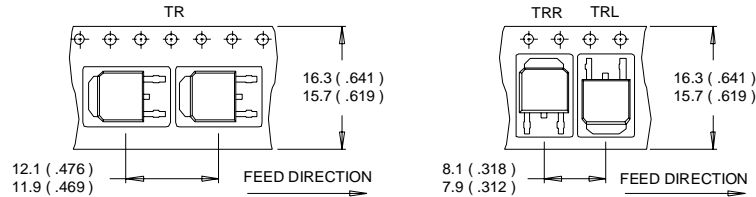


OR

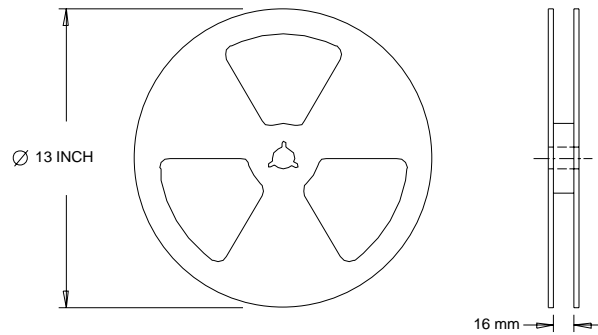


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION: MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.9\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.